

VMMBZ16C1HD1 to VMMBZ33C1HD1

Vishay Semiconductors

AUTOMOTIVE GRADE

RoHS

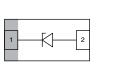
COMPLIANT

HALOGEN FREE

GREEN

(5-2008)

Single-Line Unidirectional ESD-Protection Diode in DFN1006-2A





MARKING (example only)



Bar = pin 1 marking X = date code YY = type code (see table below)

LINKS TO ADDITIONAL RESOURCES







FEATURES

- Compact DFN1006-2A package
- Low package height < 0.5 mm
- 1-line unidirectional ESD-protection
- AEC-Q101 qualified available
- Working range 14 V; 28 V
- ESD immunity acc. IEC 61000-4-2 ±15 kV to ±30 kV contact discharge ±15 kV to ±30 kV air discharge
- Lead plating: Sn (e3)
- Soldering can be checked by standard vision inspection
- AOI = Automated Optical Inspection
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

Soldering Recommendations for DFN Packages:

please see Application Note: www.vishay.com/doc?86198

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ORDERING INFORMATION						
		ENVIRONMEN	ITAL AND QUALITY CODE			
PART NUMBER (EXAMPLE)	AEC-Q101 QUALIFIED	RoHS COMPLIANT + LEAD (Pb)-FREE TERMINATIONS	TIN PLATED	10K PER 7" REEL (8 mm TAPE)	ORDERING CODE (EXAMPLE)	
		GREEN		MOQ = 10K/BOX		
VMMBZ16C1HD1	-	G	3	-08	VMMBZ16C1HD1-G3-08	
VMMBZ16C1HD1	Н	G	3	-08	VMMBZ16C1HD1HG3-08	

PACKAGE DATA								
DEVICE NAME	PACKAGE NAME	TYPE CODE	WEIGHT	MOLDING COMPOUND FLAMMABILITY RATING	MOISTURE SENSITIVITY LEVEL	SOLDERING CONDITIONS		
VMMBZ16C1HD1	DFN1006-2A	2X	0.83 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C		
VMMBZ33C1HD1	DFN1006-2A	2L	0.83 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C		



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ABSOLUTE MAXIMUM RATINGS VMMBZ16C1HD1 (T _{amb} = 25 °C, unless otherwise specified)							
PARAMETER TEST CONDITIONS SYMBOL VALUE UNIT							
Peak pulse current	Acc. IEC 61000-4-5, 8/20 µs/single shot	I _{PPM}	4	Α			
Peak pulse power	Acc. IEC 61000-4-5, 8/20 μs/single shot ⁽¹⁾	P _{PP}	108	W			
Peak pulse current	tp = 10/1000 μs ⁽¹⁾	I _{PPM}	0.7	Α			
Peak pulse power	tp = 10/1000 μs ⁽¹⁾	P _{PP}	16	W			
CCD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses (1)	M	30	kV			
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses (1)	V_{ESD}	30	kV			
Operating temperature	Junction temperature	TJ	-55 to +150	°C			
Storage temperature		T _{stg}	-55 to +150	°C			

Note

⁽¹⁾ Guaranteed by design; tested during device characterization

ABSOLUTE MAXIMUM RATINGS VMMBZ33C1HD1 (T _{amb} = 25 °C, unless otherwise specified)							
PARAMETER TEST CONDITIONS SYMBOL VALUE UNIT							
Peak pulse current	Acc. IEC 61000-4-5, 8/20 µs/single shot	I _{PPM}	1.7	Α			
Peak pulse power	Acc. IEC 61000-4-5, 8/20 μs/single shot ⁽¹⁾	P _{PP}	100	W			
Peak pulse current	tp = 10/1000 µs ⁽¹⁾	I _{PPM}	0.3	Α			
Peak pulse power	tp = 10/1000 μs ⁽¹⁾	P_{PP}	15	W			
ECD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses (1)	M	15	kV			
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses (1)	V_{ESD}	15	kV			
Operating temperature	Junction temperature	TJ	-55 to +150	°C			
Storage temperature		T _{stg}	-55 to +150	°C			

Note

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ELECTRICAL CHARACTERISTICS VMMBZ16C1HD1 (T _{amb} = 25 °C, unless otherwise specified)								
PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines		
Reverse stand off voltage	Max. reverse working voltage	V_{RWM}	-	-	14	V		
Reverse voltage	At I _R = 10 nA	V_R	14	-	-	V		
D	At V _R = 14 V	I _R	-	< 1	10	nA		
Reverse current	At $V_R = 14 \text{ V}$; $T_J = 150 ^{\circ}\text{C}^{(1)}$		-	0.06	10	μΑ		
Deverse breekdeurs veltere	At I _R = 1 mA	V_{BR}	15.2	16	16.8	V		
Reverse breakdown voltage	At $I_R = 1$ mA; $T_J = -40$ °C to $+150$ °C $^{(1)}$		14.3	_	19.0	V		
Davaraa alamaina valtaaa	At $I_{PP} = I_{PPM} = 4 \text{ A}$, $t_p = 8/20 \mu\text{s}$	V _C	19	23	27	V		
Reverse clamping voltage	t_p = 100 ns (TLP); $I_{_{TLP}}$ = 16 A $^{(1)}$	V_{C_TLP}	-	24	-	V		
Dynamic resistance	t _p = 100 ns (TLP) ⁽¹⁾	r _{dyn}	-	0.48	-	Ω		
Capacitance	At V _R = 0 V; f = 1 MHz	C _D	24.6	29	33.4	pF		

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ELECTRICAL CHARACTERISTICS VMMBZ33C1HD1 (T _{amb} = 25 °C, unless otherwise specified)								
PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines		
Reverse stand off voltage	Max. reverse working voltage	V_{RWM}	-	-	28	V		
Reverse voltage	At I _R = 10 nA	V_R	28	-	-	V		
B	At V _R = 28 V	I _R	-	< 1	10	nA		
Reverse current	At V _R = 28 V; TJ = 150 °C ⁽¹⁾		-	0.1	10	μΑ		
Devene breekdeur veltere	At I _R = 1 mA	V_{BR}	31.3	33	34.7	V		
Reverse breakdown voltage	At $I_R = 1$ mA; $T_J = -40$ °C to $+150$ °C $^{(1)}$		29	-	39	V		
Reverse clamping voltage	At $I_{PP} = I_{PPM} = 1.7 \text{ A}, t_p = 8/20 \mu \text{s}$	V _C	40	49	59	V		
	t _p = 100 ns (TLP); I _{_TLP} = 16 A ⁽¹⁾	V_{C_TLP}	-	85	-	V		
Dynamic resistance	$t_p = 100 \text{ ns (TLP)}^{(1)}$	r _{dyn}	-	0.34	-	Ω		
Capacitance	At $V_R = 0 V$; $f = 1 MHz$	C _D	13.6	16.1	18.6	pF		

Note

TYPICAL CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

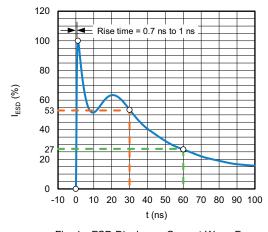


Fig. 1 - ESD Discharge Current Wave Form According to IEC 61000-4-2 (330 Ω / 150 pF)

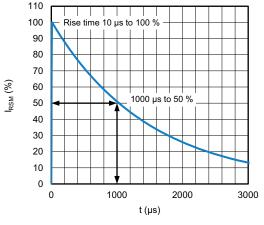


Fig. 3 - 10/1000 µs Peak Pulse Current Wave Form

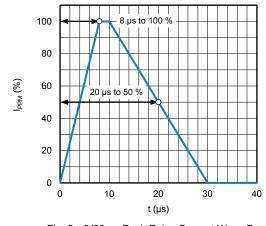


Fig. 2 - 8/20 µs Peak Pulse Current Wave Form According to IEC 61000-4-5

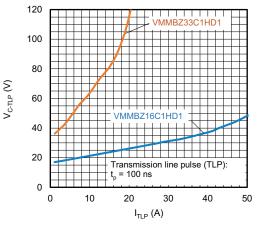


Fig. 4 - Typical Clamping Voltage vs. Peak Pulse Current

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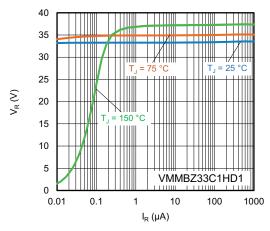


Fig. 5 - Typical Reverse Voltage vs. Reverse Current

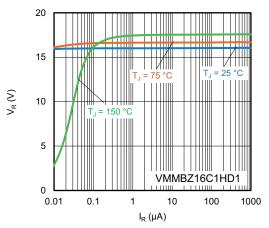


Fig. 6 - Typical Reverse Voltage vs. Reverse Current

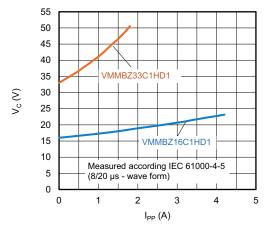


Fig. 7 - Typical Peak Clamping Voltage vs. Peak Pulse Current

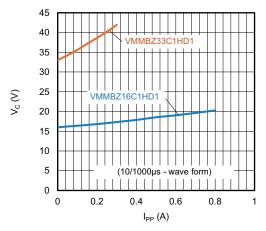


Fig. 8 - Typical Peak Clamping Voltage vs. Peak Pulse Current

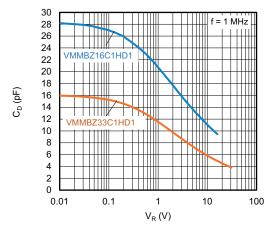


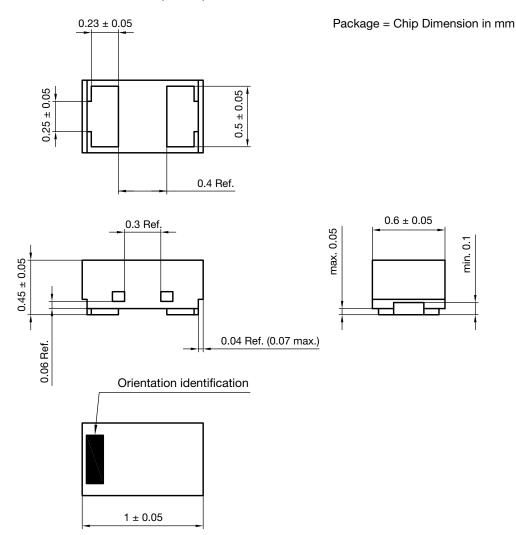
Fig. 9 - Typical Capacitance vs. Reverse Voltage

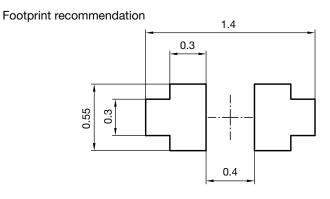




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PACKAGE DIMENSIONS in millimeters (Inches): DFN1006-2A



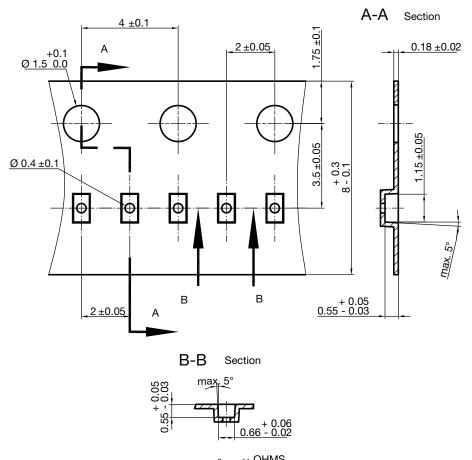


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CARRIER TAPE DFN1006-2A



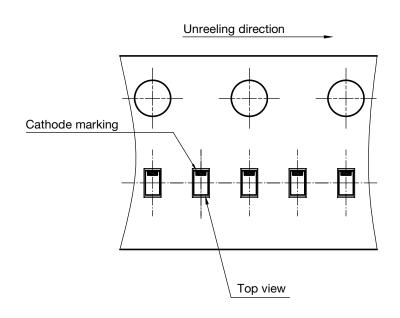
S8-V-3906.04-063 (4) created 28.10.2019

S8-V-3906.04-064 (4)

created 28.10.2019

surface resistance: 10^5 - $10^{11} \frac{OHMS}{SQ}$ Cummulative tolerances of 10 sprocket holes is ± 0.2 mm

ORIENTATION IN CARRIER TAPE DFN1006-2A



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